

English Abstract for DE2018354

Abstract :

DE2018354 A

Includes a gallium arsenide p-n interface diode generating under bias i-r radiation and provided with a phosphor for converting i-r into visible spectrum. The phosphor containing divalent ion of the Yb consists substantially of a compound in which the population state of two anion places is different in at least 1% of the phosphor. At least 5 cation % of the phosphor is of Yb³⁺, the phosphor containing one cation selected of the group 1/16% Er³⁺, 1/16% Tm³⁺ and 1/50% Ho³⁺ in min cation % rate.